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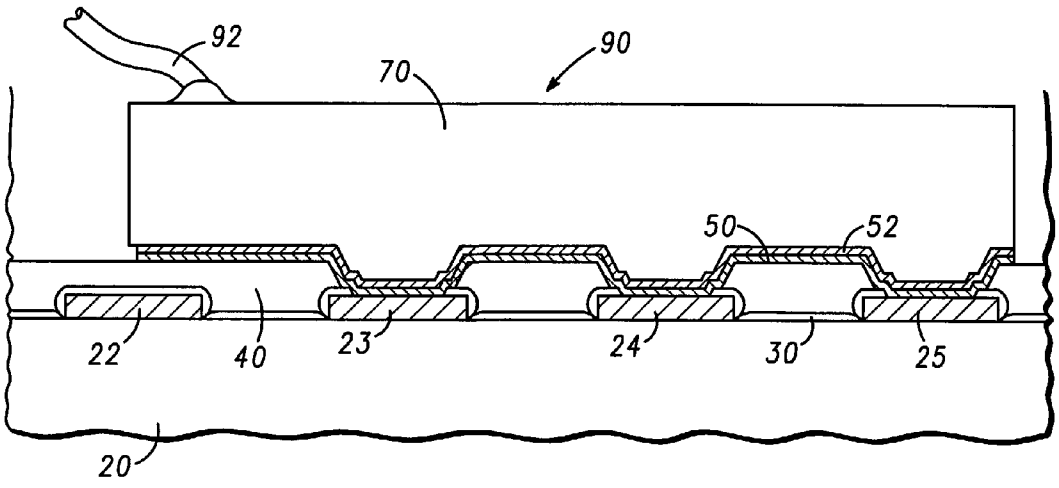
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(54) Title: SEMICONDUCTOR POWER DEVICE AND METHOD OF FORMATION



(57) Abstract: In accordance with one embodiment, a stress buffer (40) is formed between a power metal structure (90) and passivation layer (30). The stress buffer (40) reduces the effects of stress imparted upon the passivation layer (30) by the power metal structure (90). In accordance with an alternative embodiment, a power metal structure (130A) is partitioned into segments (1091), whereby electrical continuity is maintained between the segments (1090) by remaining portions of a seed layer (1052) and adhesion/barrier layer (1050). The individual segments (1090) impart a lower peak stress than a comparably sized continuous power metal structure (9).

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